

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	22	(method and semiconductor and device and form and first and second and gate and electrode and (insulat\$3 or dielectric) and (layer or film) and source and drain and organic and material and etch).clm.	US-PGPUB; USPAT; USOCR	OR	ON	2009/06/09 13:20

6/ 9/ 2009 2:07:49 PM**C:\ Documents and Settings\ aho1\ My Documents\ EAST\ Workspaces\ 10573328.
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